

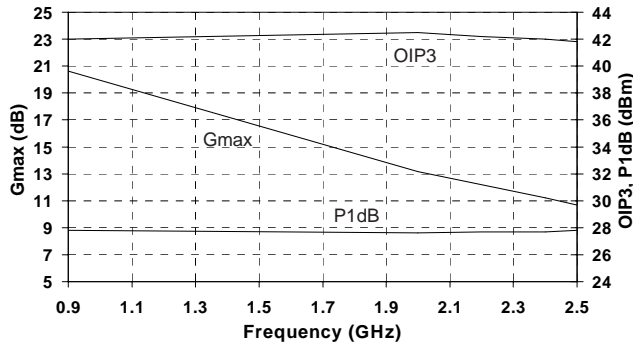


Product Description

Sirenza Microdevices' SGA-9289 is a high performance transistor designed for operation to 3 GHz. With optimal matching at 2 GHz, OIP₃=42.5 dBm and P_{1dB}=27.5 dBm. This RF device is based on a Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process. The SGA-9289 is cost-effective for applications requiring high linearity even at moderate biasing levels. It is well suited for operation at both 5V and 3V.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.

Typical G_{max}, OIP₃, P_{1dB} @ 5V, 270mA



SGA-9289 SGA-9289Z



Medium Power Discrete SiGe Transistor



Product Features

- Available in RoHS compliant Green packaging
- 50-3000 MHz Operation
- 42.5 dBm Output IP₃ Typical at 1.96 GHz
- 12.0 dB Gain Typical at 1.96 GHz
- 27.5 dBm P_{1dB} Typical at 1.96 GHz
- 2.4 dB NF Typical at 0.9 GHz
- Cost Effective
- 3-5 V Operation

Applications

- Wireless Infrastructure Driver Amplifiers
- CATV Amplifiers
- Wireless Data, WLL Amplifiers
- AN-022 contains detailed application circuits

Symbol	Device Characteristics, T = 25°C V _{CE} = 5V, I _{CQ} = 280mA (unless otherwise noted)	Test Frequency [1] 100% Tested [2] Sample Tested	Units	Min.	Typ.	Max.
G _{MAX}	Maximum Available Gain Z _S =Z _S [*] , Z _L =Z _L [*]	f = 900 MHz f = 1960 MHz	dB		20.5 13.1	
G	Power Gain Z _S =Z _{SOPT} , Z _L =Z _{LOPT}	f = 900 MHz [1] f = 1960 MHz [2]	dB	16.2 11.0	17.7 12.0	19.2 13.0
P _{1dB}	Output 1dB Compression Point Z _S =Z _{SOPT} , Z _L =Z _{LOPT}	f = 900 MHz f = 1960 MHz [2]	dBm	26.0	28.0 27.5	
OIP ₃	Output Third Order Intercept Point Z _S =Z _{SOPT} , Z _L =Z _{LOPT} , P _{OUT} = +13 dBm per tone	f = 900 MHz f = 1960 MHz [2]	dBm	40.0	42.0 42.5	
NF	Noise Figure Z _S =Z _{SOPT} , Z _L =Z _{LOPT}	f = 900 MHz f = 1960 MHz	dB		2.4 2.5	
BV _{CEO}	Collector - Emitter Breakdown Voltage		V	7.5	8.5	
h _{FE}	DC current gain			100	180	300
R _{th}	Thermal Resistance (junction-to-lead)		°C/W		32	
V _{CE}	Operating Voltage (collector-to-emitter)		V			5.5
I	Operating Current		mA	250	280	320

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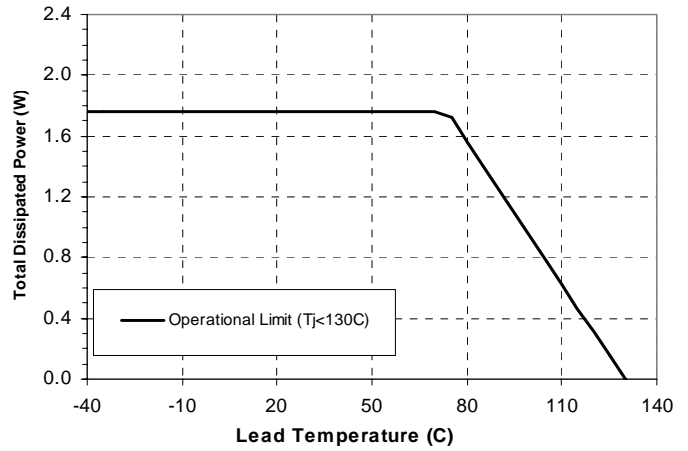
SGA-9289 Medium Power Discrete SiGe Transistor

Absolute Maximum Ratings

Parameter	Absolute Limit
Max Base Current (I_B)	10 mA
Max Device Current (I_{CE})	400 mA
Max Collector-Emitter Voltage (V_{CEO})	7 V
Max Collector-Base Voltage (V_{CBO})	20 V
Max Emitter-Base Voltage (V_{EBO})	4.8 V
Max. Junction Temp. (T_J)	+150°C
Operating Temp. Range (T_L)	See Graph
Max. Storage Temp.	+150°C

***Note:** Load condition, $Z_L = 50$ Ohms
 Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.
 Bias Conditions should also satisfy the following expression:
 $I_D V_D < (T_J - T_L) / R_{TH, j-l} \quad T_L = T_{LEAD}$

Maximum Recommended Operational Dissipated Power



Typical Performance - Engineering Application Circuits (See AN-022)

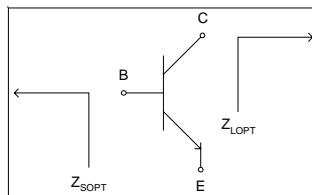
Freq (MHz)	V_{CE} (V)	I_{CQ} (mA)	P1dB (dBm)	OIP3 ¹ (dBm)	Gain (dB)	S11 (dB)	S22 (dB)	NF (dB)	Z_{SOPT} (Ω)	Z_{LOPT} (Ω)
945	5	287	27.8	42.0	17.8	-19	-11	2.5	2.93 - j3.92	15.81 + j1.57
1960	5	292	27.5	42.0	12.1	-24	-21	2.5	4.75 - j9.12	10.3 - j4.87
2140	5	293	27.7	42.0	11.1	-11	-20	2.8	4.30 - j9.09	13.4 + j2.31
2440	5	287	27.5	42.0	9.8	-17	-20	3.0	4.05 - j13.78	11.76 - j9.2

¹ $P_{OUT} = +13$ dBm per tone for $V_{CE} = 5V$, 1 MHz tone spacing

Freq (MHz)	V_{CE} (V)	I_{CQ} (mA)	P1dB (dBm)	OIP3 ² (dBm)	Gain (dB)	S11 (dB)	S22 (dB)	NF (dB)	Z_{SOPT} (Ω)	Z_{LOPT} (Ω)
945	3	312	25.4	38.6	16.8	-18	-9	2.6	5.61 - j4.75	6.51 + j2.58
1960	3	315	26.0	39.3	11.0	-18	-15	2.9	3.23 - j5.67	4.95 + j1.73
2440	3	315	26.1	38.0	9.4	-29	-17	3.4	4.07 - j14.25	11.62 - j11.83

² $P_{OUT} = +10$ dBm per tone for $V_{CE} = 3V$, 1 MHz tone spacing

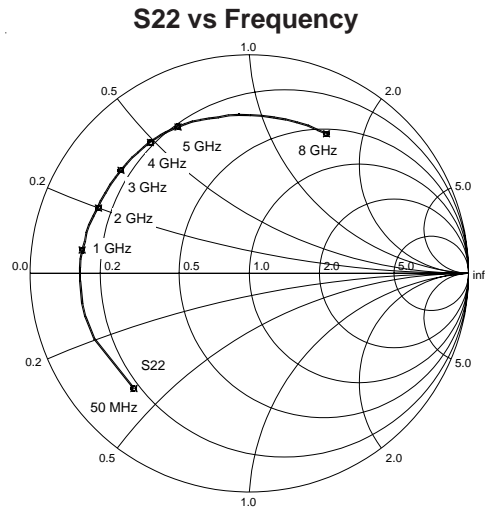
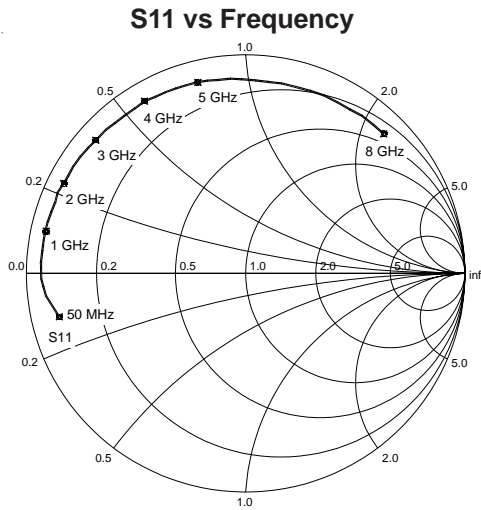
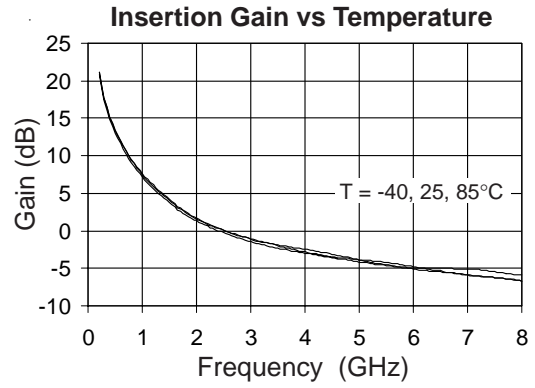
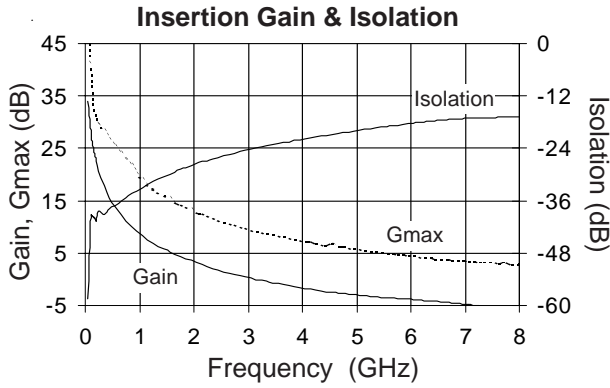
Data above represents typical performance of the application circuits noted in Application Note AN-022. Refer to the application note for additional RF data, PCB layouts, and BOMs for each application circuit. The application note also includes biasing instructions and other key issues to be considered. For the latest application notes please visit our site at www.sirenza.com or call your local sales representative.



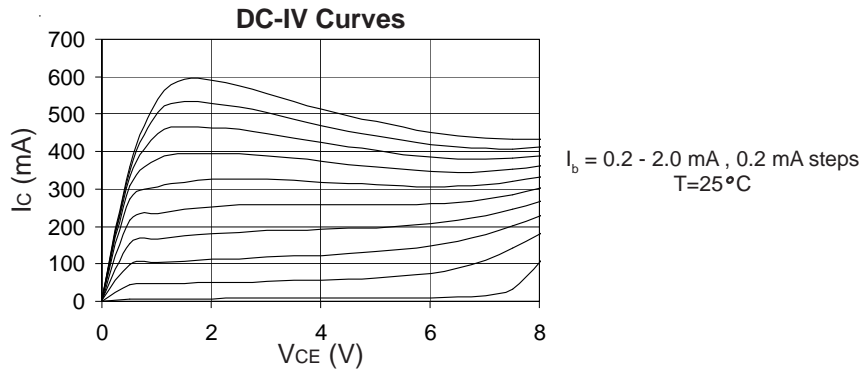


SGA-9289 Medium Power Discrete SiGe Transistor

De-embedded S-Parameters ($Z_S=Z_L=50\ \Omega$, $V_{CE}=5V$, $I_{CQ}=270mA$, $25^\circ C$)



Note: S-parameters are de-embedded to the device leads with $Z_S=Z_L=50\ \Omega$. The data represents typical performance of the device. De-embedded s-parameters can be downloaded from our website (www.sirenza.com).





SGA-9289 Medium Power Discrete SiGe Transistor



Caution: ESD sensitive
Appropriate precautions in handling, packaging and testing devices must be observed.

Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-9289	13"	3000
SGA-9289Z	13"	3000

Pin Description

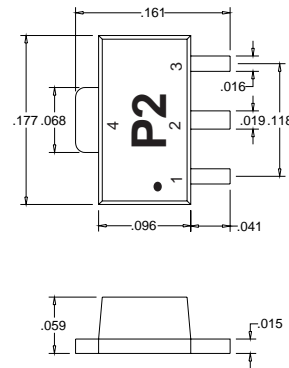
Pin #	Function	Description
1	Base	RF Input
2	Emitter	Connection to ground. Use via holes to reduce lead inductance. Place vias as close to ground leads as possible.
3	Collector	RF Output
4	Emitter	Same as Pin 2

Mounting and Thermal Considerations

It is very important that adequate heat sinking be provided to minimize the device junction temperature. The following items should be implemented to maximize MTTF and RF performance.

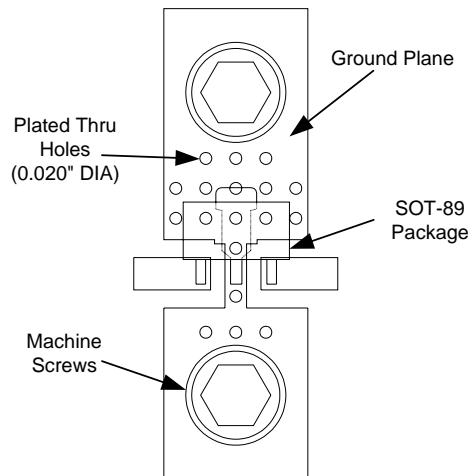
1. Multiple solder-filled vias are required directly below the ground tab (pin 4). [CRITICAL]
2. Incorporate a large ground pad area with multiple plated-through vias around pin 4 of the device. [CRITICAL]
3. Use two point board seating to lower the thermal resistance between the PCB and mounting plate. Place machine screws as close to the ground tab (pin 4) as possible. [RECOMMENDED]
4. Use 2 ounce copper to improve the PCB's heat spreading capability. [RECOMMENDED]

Package Dimensions



DIMENSIONS ARE IN INCHES

Recommended Mounting Configuration for Optimum RF and Thermal Performance



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